



# BT134-600E

## 4Q Triac

21 November 2013

Product data sheet

## 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT82 plastic package intended for use in general purpose bidirectional switching and phase control applications. This "series E" sensitive gate triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- Compact package
- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control

## 4. Quick reference data

Table 1. Quick reference data

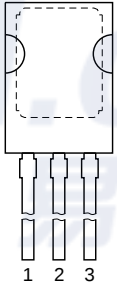
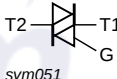
| Symbol                        | Parameter                            | Conditions                                                                                                                                                 | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| $V_{\text{DRM}}$              | repetitive peak off-state voltage    |                                                                                                                                                            | -   | -   | 600 | V    |
| $I_{\text{TSM}}$              | non-repetitive peak on-state current | full sine wave; $T_{\text{J}(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 25  | A    |
| $I_{\text{T(RMS)}}$           | RMS on-state current                 | full sine wave; $T_{\text{mb}} \leq 107\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>                | -   | -   | 4   | A    |
| <b>Static characteristics</b> |                                      |                                                                                                                                                            |     |     |     |      |
| $I_{\text{GT}}$               | gate trigger current                 | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; $T_2 + G+$ ; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>           | -   | 2.5 | 10  | mA   |



| Symbol | Parameter       | Conditions                                                                                        | Min | Typ | Max | Unit |
|--------|-----------------|---------------------------------------------------------------------------------------------------|-----|-----|-----|------|
|        |                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7 | -   | 4   | 10  | mA   |
|        |                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7 | -   | 5   | 10  | mA   |
|        |                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7 | -   | 11  | 25  | mA   |
| $I_H$  | holding current | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 9                                   | -   | 2.2 | 15  | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline                                                                                     | Graphic symbol                                                                      |
|-----|--------|--------------------------------|--------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | T1     | main terminal 1                |  <p>SIP3 (SOT82)</p> |  |
| 2   | T2     | main terminal 2                |                                                                                                        |                                                                                     |
| 3   | G      | gate                           |                                                                                                        |                                                                                     |
| mb  | T2     | mounting base; main terminal 2 |                                                                                                        |                                                                                     |

## 6. Ordering information

Table 3. Ordering information

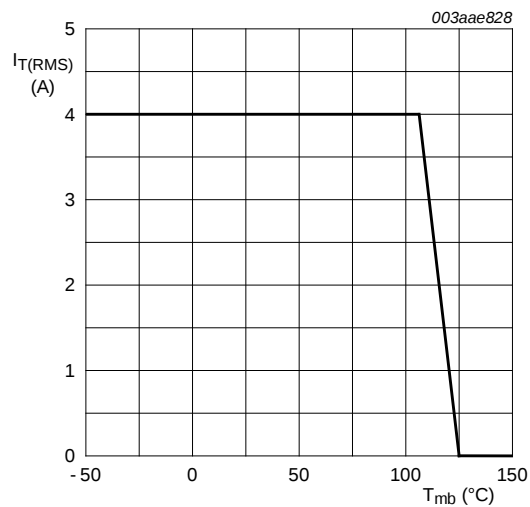
| Type number | Package |                                                 |         |
|-------------|---------|-------------------------------------------------|---------|
|             | Name    | Description                                     | Version |
| BT134-600E  | SIP3    | plastic single-ended package; 3 leads (in-line) | SOT82   |

## 7. Limiting values

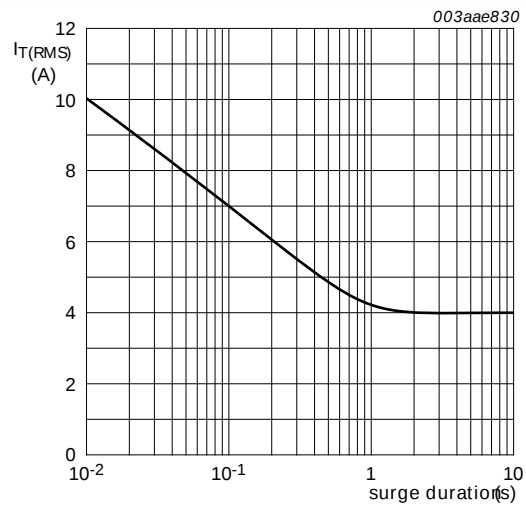
**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol              | Parameter                            | Conditions                                                                                                                                          | Min | Max | Unit                   |
|---------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |                                                                                                                                                     | -   | 600 | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{mb}} \leq 107\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>         | -   | 4   | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 25  | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$                                                 | -   | 27  | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_{\text{p}} = 10\text{ ms}$ ; SIN                                                                                                                 | -   | 3.1 | $\text{A}^2\text{s}$   |
| $di_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G+                                | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G-                                | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G-                                | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 6\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dI_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G+                                | -   | 10  | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |                                                                                                                                                     | -   | 2   | A                      |
| $P_{\text{GM}}$     | peak gate power                      |                                                                                                                                                     | -   | 5   | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period                                                                                                                               | -   | 0.5 | W                      |
| $T_{\text{stg}}$    | storage temperature                  |                                                                                                                                                     | -40 | 150 | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |                                                                                                                                                     | -   | 125 | $^{\circ}\text{C}$     |

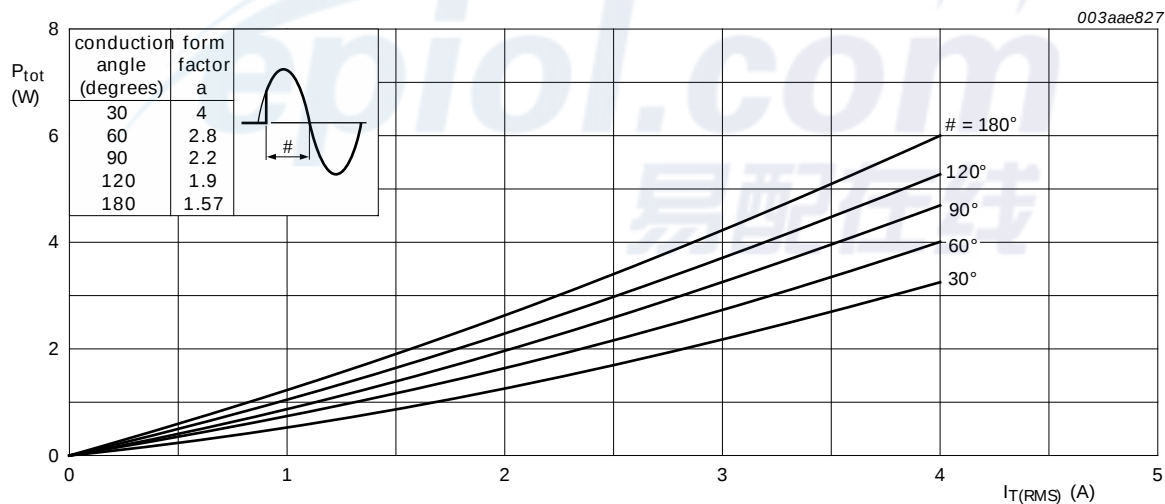


**Fig. 1.** RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$   
 $T_{mb} \leq 107\text{ °C}$

**Fig. 2.** RMS on-state current as a function of surge duration; maximum values



$\alpha$  = conduction angle  
 $a$  = form factor =  $I_{T(RMS)} / I_{T(AV)}$

**Fig. 3.** Total power dissipation as a function of RMS on-state current; maximum values

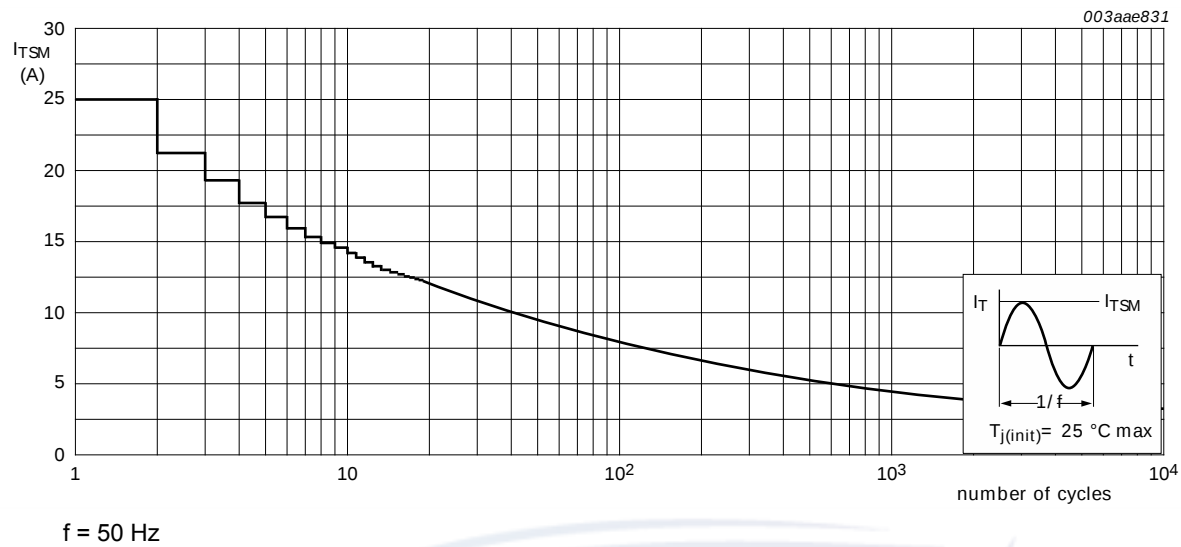


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                         | Conditions         | Min | Typ | Max | Unit |
|----------------|---------------------------------------------------|--------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | half cycle; Fig. 6 | -   | -   | 3.7 | K/W  |
|                |                                                   | full cycle; Fig. 6 | -   | -   | 3   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air        | -   | 100 | -   | K/W  |

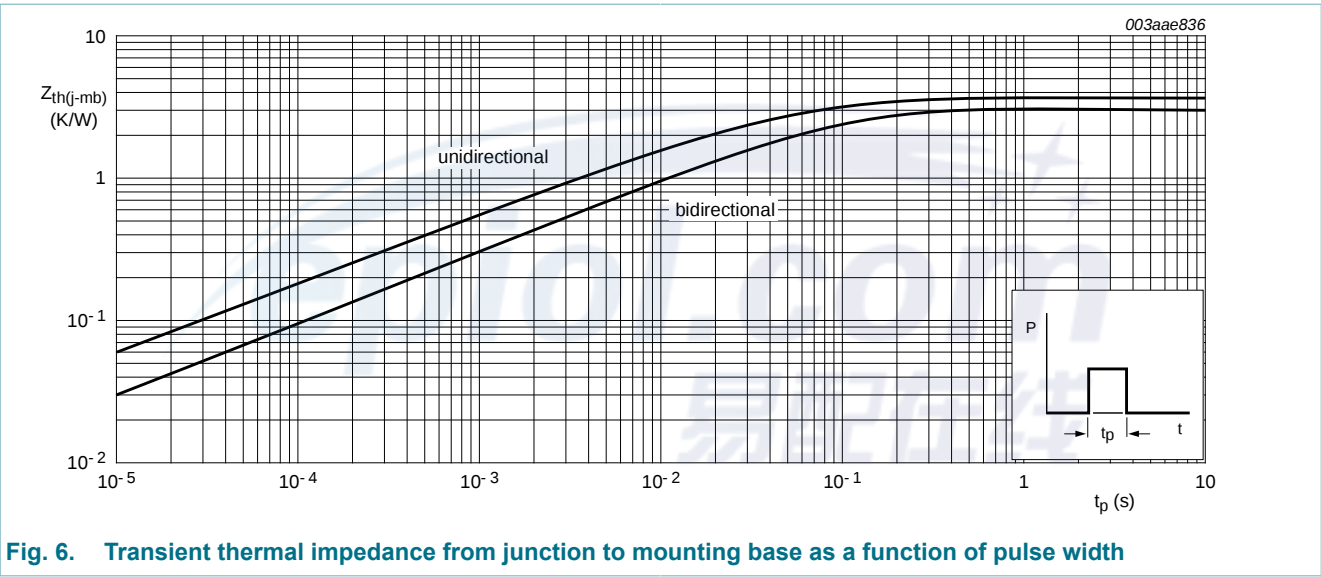
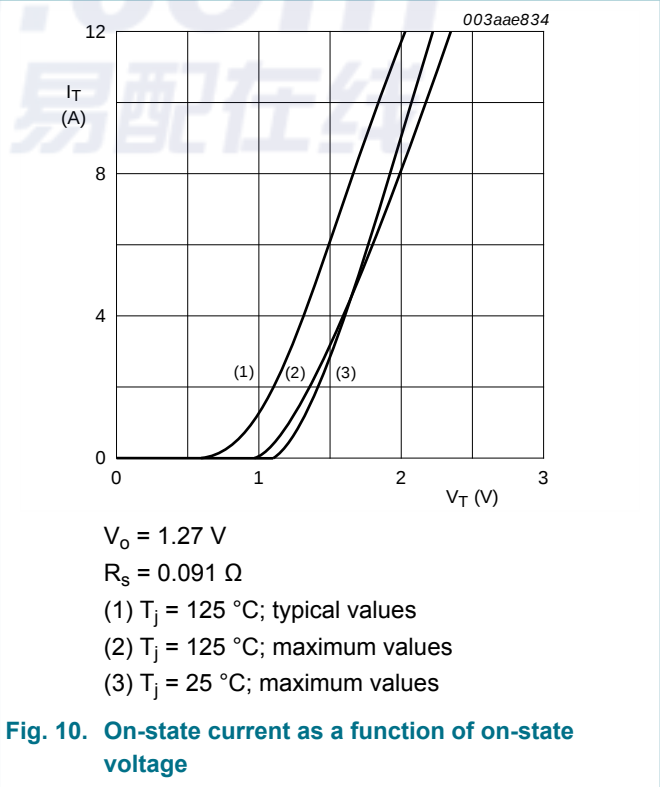
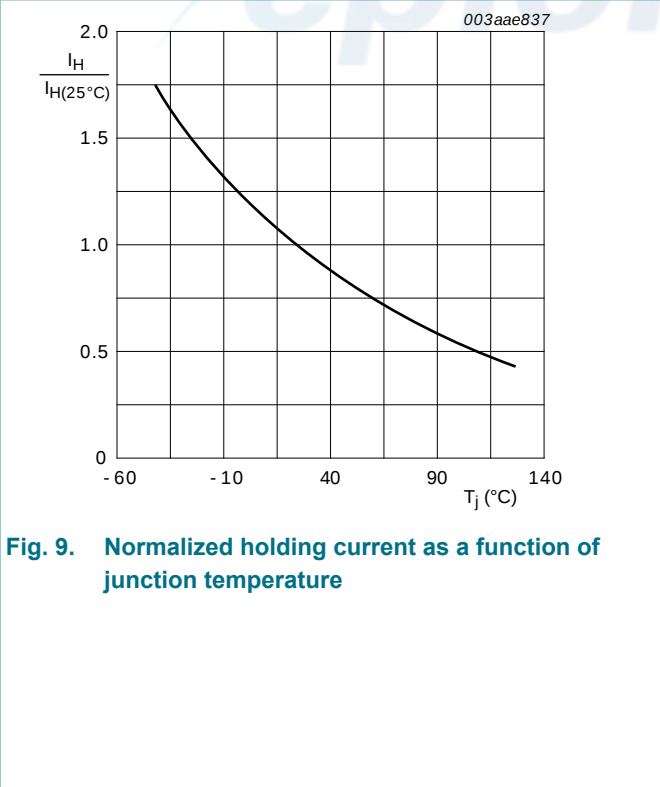
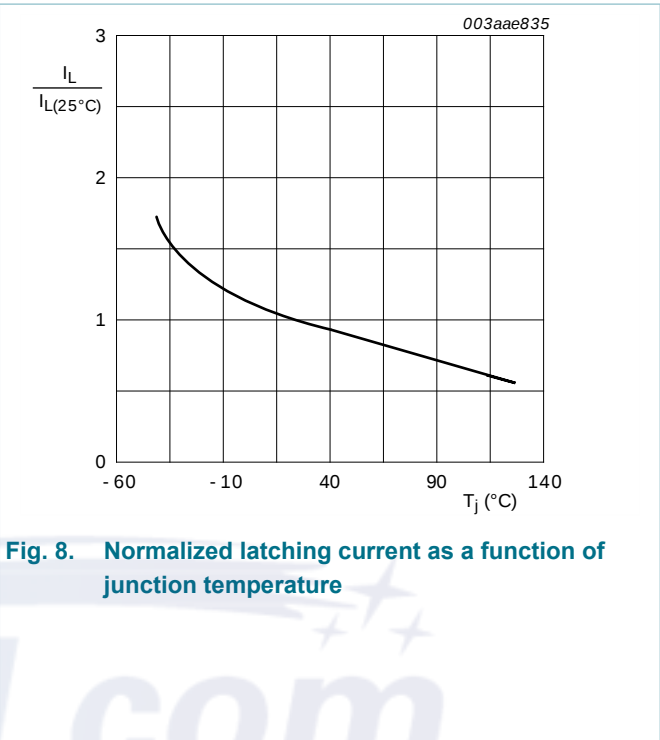
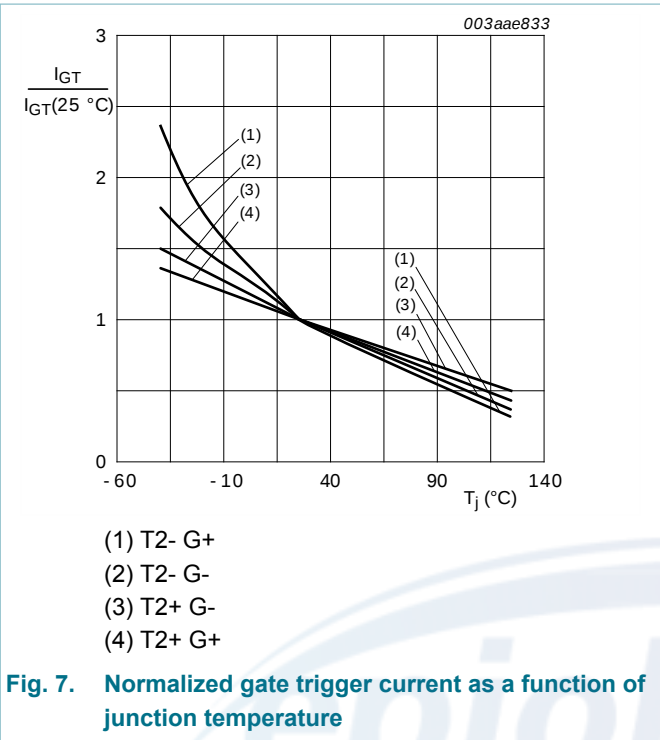


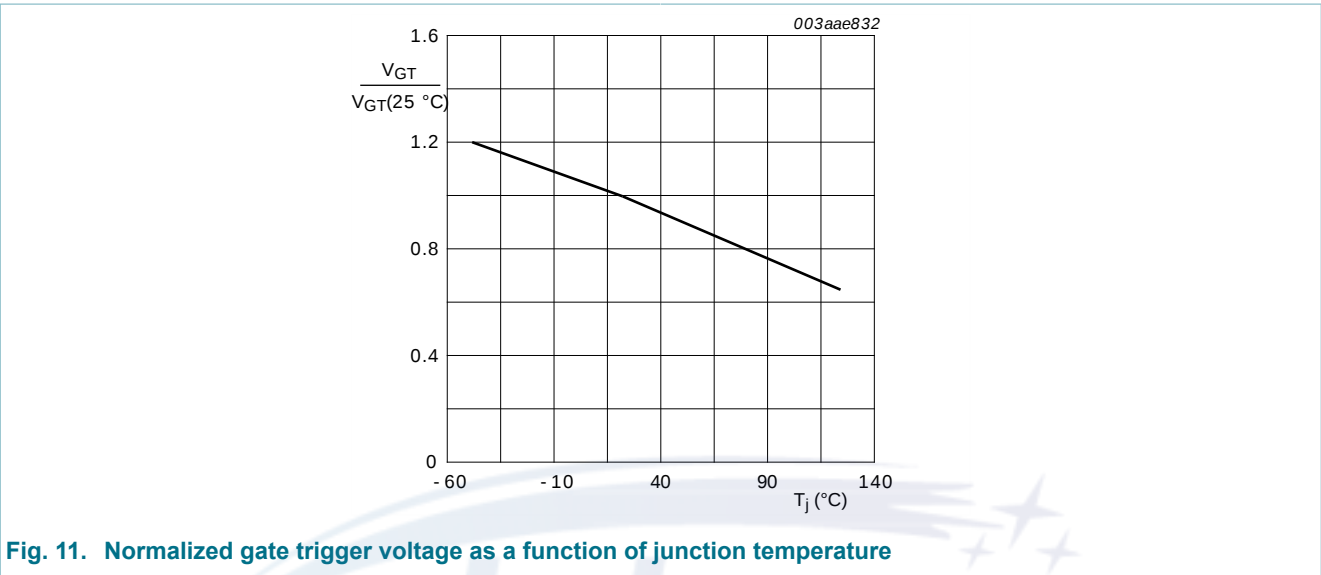
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                         | Conditions                                                                                                                              | Min  | Typ | Max | Unit             |
|--------------------------------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|------|-----|-----|------------------|
| <b>Static characteristics</b>  |                                   |                                                                                                                                         |      |     |     |                  |
| $I_{GT}$                       | gate trigger current              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 2.5 | 10  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 4   | 10  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 5   | 10  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 11  | 25  | mA               |
| $I_L$                          | latching current                  | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 3   | 15  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 10  | 20  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 2.5 | 15  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 4   | 20  | mA               |
| $I_H$                          | holding current                   | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>                                                         | -    | 2.2 | 15  | mA               |
| $V_T$                          | on-state voltage                  | $I_T = 5\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                                         | -    | 1.4 | 1.7 | V                |
| $V_{GT}$                       | gate trigger voltage              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                              | -    | 0.7 | 1   | V                |
|                                |                                   | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                            | 0.25 | 0.4 | -   | V                |
| $I_D$                          | off-state current                 | $V_D = 600\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                                                | -    | 0.1 | 0.5 | mA               |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                         |      |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | -    | 50  | -   | V/ $\mu\text{s}$ |
| $t_{gt}$                       | gate-controlled turn-on time      | $I_{TM} = 6\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$                                | -    | 2   | -   | $\mu\text{s}$    |

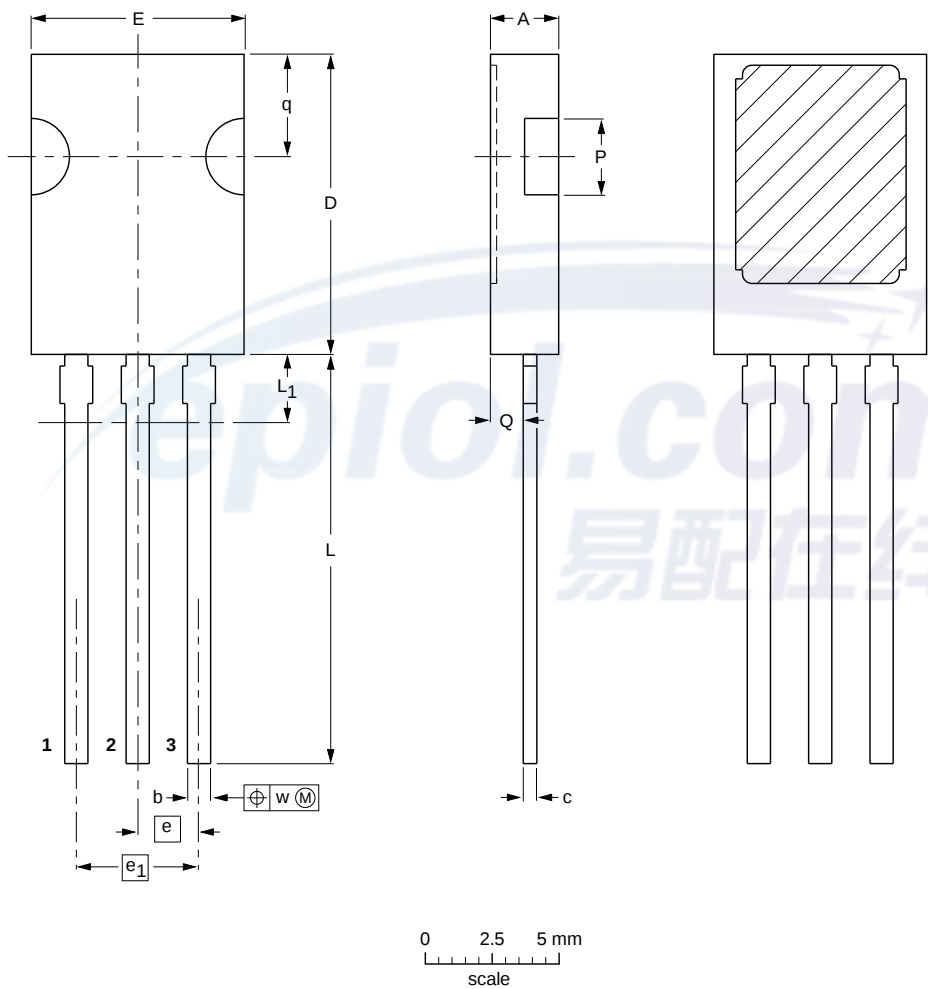




10. Package outline

Plastic single-ended package; 3 leads (in-line)

SOT82



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | b            | c            | D            | E          | e    | e <sub>1</sub> | L            | L <sub>1</sub> <sup>(1)</sup><br>max. | P          | Q          | q          | w     |
|------|------------|--------------|--------------|--------------|------------|------|----------------|--------------|---------------------------------------|------------|------------|------------|-------|
| mm   | 2.8<br>2.3 | 0.88<br>0.65 | 0.58<br>0.47 | 11.1<br>10.5 | 7.8<br>7.2 | 2.29 | 4.58           | 16.5<br>15.3 | 2.54                                  | 3.1<br>2.5 | 1.5<br>0.9 | 3.9<br>3.5 | 0.254 |

Note

1. Terminal dimensions within this zone are uncontrolled to allow for body and terminal irregularities.

| OUTLINE<br>VERSION | REFERENCES |       |      |  | EUROPEAN<br>PROJECTION | ISSUE DATE |
|--------------------|------------|-------|------|--|------------------------|------------|
|                    | IEC        | JEDEC | EIAJ |  |                        |            |
| SOT82              |            |       |      |  |                        | 97-06-11   |

Fig. 12. Package outline SIP3 (SOT82)

## 11. Legal information

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| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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